

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE


Application No. : CONTINUATION OF 09/916,555  
Applicant : Chih Hsin Wang et al.  
Filed : HEREWITH  
TC/A.U. : 2814  
Examiner : M. D. Pizarro-Crespo  
Title : A SEMICONDUCTOR MEMORY ARRAY OF FLOATING  
GATE MEMORY CELLS WITH LOW RESISTANCE SOURCE  
REGIONS AND HIGH SOURCE COUPLING  
(as amended)  
  
Docket No. : 2102397-911401  
Customer No. : 26379

MAIL STOP PATENT APPLICATION  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited with the United States Postal Service as EXPRESS MAIL (EV 302278047 US) in an envelope addressed to Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on October 20, 2003.

GRAY CARY WARE & FREIDENRICH Date: 10/20/03

By:   
Susan Pingue

**PRELIMINARY AMENDMENT**

Sir:

Please preliminarily amend the above identified application as follows:

**Amendments to the Specification** begin on page 2 of this paper.

**Amendments to the Claims** are reflected in the listing of claims which begins on page 4 of this paper.

**Remarks/Arguments** begin on page 8 of this paper.